MICROWAVE POWER GaN AMPLIFIER

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

•BROAD BAND 2-STAGE AMPLIFIER •HIGH POWER Pout= 44.0dBm at Pin= 23.0dBm •HIGH GAIN GL= 24dB(Typ) at Pin= 7dBm

HERMETICALLY SEALED PACKAGE



TGM9398-25

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDD1,VDD2= 24V IDDset= 1.2A @Pin= 23.0dBm f = 9.3 to 9.8GHz	dBm	43.0	44.0	_
Drain Current	IDD*		А	_	2.6	3.5
Power Added Efficiency	ηadd		%		38	
Linear Gain	GL	@Pin= 7dBm	dB	20	24	

*IDD=IDD1+ IDD2

ABSOLUTE MAXIMUM RATINGS (Ta= 25° C)

CHARACTERISTICS	SYMBOL	UNIT	RATING	
Drain- Source Voltage	VDD1, VDD2	V	50	
Gate- Source Voltage	VGG1,VGG2	V	-10	
	IDD1	A	1.25	
Drain Current	IDD2	A	7.5	
Flange Temperature	Tf	°C	-40 to +90	
Input Power	Pin	dBm	+27	
Storage Temperature	Tstg	°C	-65 to +175	

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MICROWAVE SEMICONDUCTOR TECHNICAL DATA PACKAGE OUTLINE (7-BA42B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds 350°C. Flanges of devices should be attached using screws and washers. Recommended torque is 0.18-0.20 N·m.

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

Pout , Gain , PAE , IDS vs. Pin

VDS= 24 V, IDDset= 1.2 A, f= 9.3, 9.55, 9.8 GHz, Ta= +25 °C









MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout , Gain , PAE , IDS vs. Pin vs. Temperature

VDS= 24 V, IDDset= 1.2 A, f= 9.55 GHz, Ta= -20, +25, +80 °C









MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·S-Parameters

VDS= 24 V, IDDset= 1.2 A, f= 8.0 to 11.0 GHz, Ta= +25 °C







S21, S12 VDS=24V, IDD=1.2A S21 S12 11 10



MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MEASUREMENT CIRCUIT SCHEMATIC



MICROWAVE SEMICONDUCTOR TECHNICAL DATA RESTRICTIONS ON PRODUCT USE

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